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### 1. 概要(Summary)

金蒸着後、電子ビームリソグラフィとリフトオフプロセスにより 10 nm の金ナノドットを作製した。

# 2. 実験(Experimental)

【利用した主な装置】超高速大面積電子線描画装置 F7000S-VD02、8 インチ汎用スパッタ装置

## 【実験方法】

ナノドットの電子ビーム描画 $(3\sim6$  時間)、8 nm 金蒸着 3. 結果と考察(Results and Discussion)

We could successfully fabricate 10-15 nm diameter gold nanodots with a combination of e-beam lithography (Advantest F7000-VD02), evaporation and Lift-off process (Fig.1). We aim at patterning arrays of 10nm dots on 4 inch wafer. The process has been adapted from the one described in [1]. with the use of 40 nm-thick ZEP instead of PMMA 950K. For such thin ZEP layer, the usual ZEP remover does not provide the optimum result for the lift-off process, so other removers have to be tested. The e-beam Advantest F7000 writing speed for 10 nm-dot arrays is substantially improved compared to results published in [1], thanks to the "on-the-fly" writing ability. This enabled the fabrication of nanodot arrays over several cm2. However, if we compare to state-of-the-art e-beam writing speed for such nanodot arrays [2], with studies specifically dedicated to that purpose, the actual writing speed remains few times slower. The present limitation is the maximum available beam current density (100A/cm<sup>2</sup>), which corresponds to 100 pA for a single 10 nm × 10 nm dots, whereas optimized currents for 10 nm × 10 nm dots have

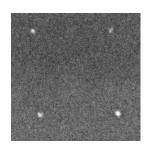


Fig. 1 SEM image of 10 nm diameter dots obtained by e-beam lithography. Interdots spacing is 200 nm.

been estimated to 1 nA [2]. This could potentially be improved significantly in the future by using additional hard masks that contain the pattern to be exposed.

To conclude, we have shown the possibility to fabricate 10-15 nm diameter dots and identified potential strategies to improve both the homogeneity of the lift-off process and the writing speed of such arrays. In addition, we plan to extend this process to glass substrates towards the development of single-biomolecule sensor arrays.

#### 4. その他・特記事項(Others)

## References:

[1] N. Clement, G. Patriarche, K. Smaali, F. Vaurette, K. Nishiguchi, D. Troadec, A. Fujiwara, and D. Vuillaume, Large-array of sub-10 nm single grain Au nanodots for use in Nanotechnology, Small 7, 2607 (2011)

[2] J. Trasobares, D. Vuillaume, D. Theron, and N. Clement, A 17 GHz Molecular Rectifier, Nature Communications, 7, 12850 (2016)

5. 論文・学会発表 (Publication/Presentation)

### 6. 関連特許(Patent)

なし